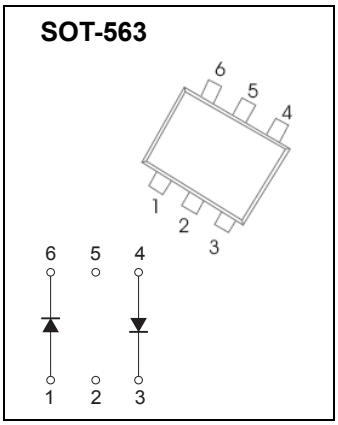
Plastic-Encapsulate Diodes

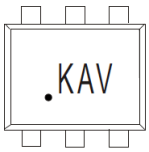
SCHOTTKY BARRIER DIODE

FEATURES

Surface mount schottky barrier diode arrays



Marking: KAV



Solid dot = Pin1 indicate.

Maximum Ratings @Ta=25℃

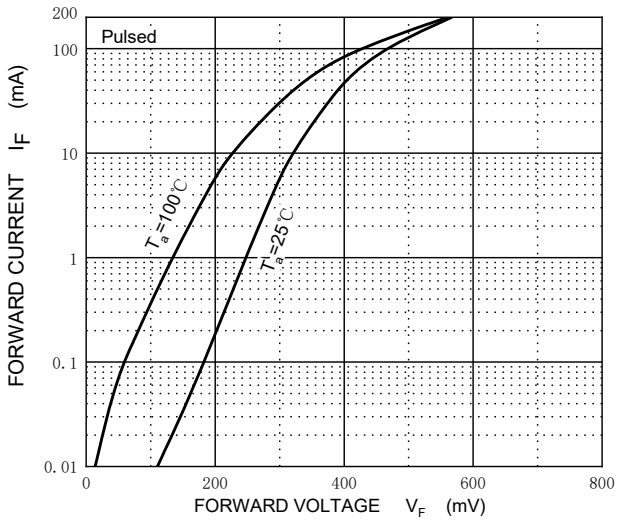
Parameter	Symbol	Limit	Unit
Peak Repetitive Peak Reverse Voltage **Working Peak Reverse Voltage** **DC Blocking V oltage**	V_{RRM} V_{RWM} V_R	30	V
Average Rectified Output Current	I_O	200	mA
Non-repetitive Peak Forward Surge Current @ t=8.3ms	I_{FSM}	600	mA
Repetitive Peak Forward Current @ t≤1s, δ ≤0.5	I_{FRM}	300	mA
Power Dissipation	P_D	150	mW
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	667	℃/W
Operating Junction Temperature Range	T_J	-40 ~ +125	℃
Storage Temperature Range	T_{STG}	-55 ~ +125	℃

ELECTRICAL CHARACTERISTICS (Ta=25℃ unless otherwise specified)

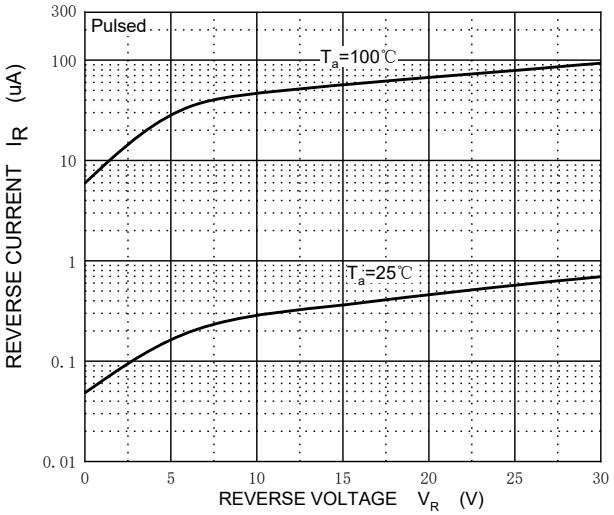
Parameter	Symbol	Test conditions	Min	Max	Unit
Reverse breakdown voltage	$V_{(BR)}$	I_R= 100μA	30		V
Reverse voltage leakag e current	I_R	V_R=25V		2	uA
Forward voltage	V_F	I_F=1mA I_F=10mA I_F=30mA I_F=100mA		320 400 500 1000	mV
Total capacitance	C_T	V_R=1V,f=1MHz		15	pF
Reverse recovery time	t_{rr}	I_F=10mA, I_R=10mA~1mA R_L=100Ω		5	ns

Typical Characteristics

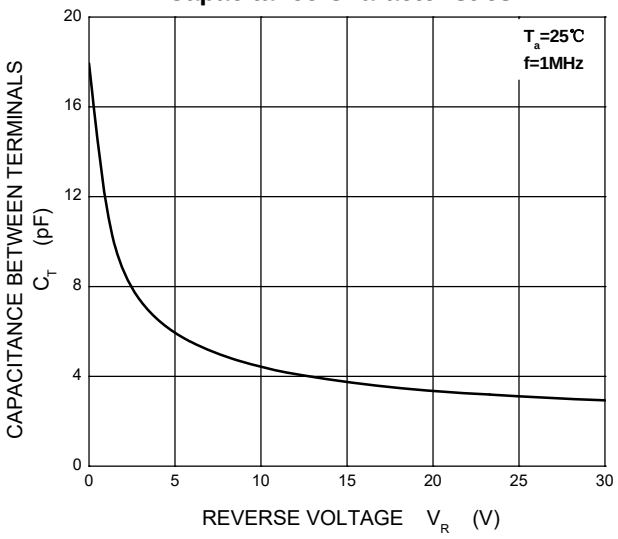
Forward Characteristics



Reverse Characteristics



Capacitance Characteristics



Power Derating Curve